

SQ2308CES-T1_GE3 Datasheet



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DiGi Electronics Part Number SQ2308CES-T1_GE3-DG

Manufacturer Vishay Siliconix

Manufacturer Product Number SQ2308CES-T1_GE3

Description MOSFET N-CH 60V 2.3A SOT23

Detailed Description N-Channel 60 V 2.3A (Tc) 2W (Tc) Surface Mount SO

T-23-3 (TO-236)



Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

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Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
SQ2308CES-T1_GE3	Vishay Siliconix
Series:	Product Status:
TrenchFET®	Active
FET Type:	Technology:
N-Channel	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss):	Current - Continuous Drain (Id) @ 25°C:
60 V	2.3A (Tc)
Drive Voltage (Max Rds On, Min Rds On):	Rds On (Max) @ Id, Vgs:
4.5V, 10V	150mOhm @ 2.3A, 10V
Vgs(th) (Max) @ ld:	Gate Charge (Qg) (Max) @ Vgs:
2.5V @ 250μA	5.3 nC @ 10 V
Vgs (Max):	Input Capacitance (Ciss) (Max) @ Vds:
±20V	205 pF @ 30 V
FET Feature:	Power Dissipation (Max):
	2W (Tc)
Operating Temperature:	Grade:
-55°C ~ 175°C (TJ)	Automotive
Qualification:	Mounting Type:
AEC-Q101	Surface Mount
Supplier Device Package:	Package / Case:
SOT-23-3 (TO-236)	TO-236-3, SC-59, SOT-23-3
Base Product Number:	
SQ2308	

Environmental & Export classification

8541.29.0095

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
Vendor Undefined	EAR99
HTSUS:	





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Automotive N-Channel 60 V (D-S) 175 °C MOSFET



Marking Code: 8X

PRODUCT SUMMARY					
V _{DS} (V)	60				
$R_{DS(on)}$ (Ω) at $V_{GS} = 10 \text{ V}$	0.150				
$R_{DS(on)}$ (Ω) at $V_{GS} = 4.5 \text{ V}$	0.164				
I _D (A)	2.3				
Configuration	Single				

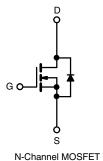
FEATURES

- TrenchFET® Power MOSFET
- AEC-Q101 Qualified ^c
- 100 % Rq and UIS Tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912









ORDERING INFORMATION					
Package	SOT-23				
Lead (Pb)-free and halogen-free	SQ2308CES (for detailed order number please see www.vishay.com/doc?79771)				

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)					
PARAMETER	SYMBOL	LIMIT	UNIT		
Drain-source voltage		V _{DS}	60	V	
Gate-source voltage		V_{GS}	± 20	V	
Continuous dusin surrent	T _C = 25 °C	- I _D	2.3		
Continuous drain current	T _C = 125 °C		1.3		
Continuous source current (diode conduction)		I _S	2.4	Α	
Pulsed drain current ^a		I _{DM}	9		
Single pulse avalanche current	L = 0.1 mH	I _{AS}	7		
Single pulse avalanche energy	L = U.1 MH	E _{AS}	2.5	mJ	
	T _C = 25 °C	P _D	2	14/	
Maximum power dissipation ^a	T _C = 125 °C		0.6	W	
Operating junction and storage temperature	T _J , T _{stq}	-55 to +175	°C		

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-ambient	PCB mount b	R_{thJA}	120	°C/W
Junction-to-foot (drain)		R _{thJF}	80	G/ VV

Notes

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %
- b. When mounted on 1" square PCB (FR-4 material)
- c. Parametric verification ongoing



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PARAMETER	SYMBOL	TES	TEST CONDITIONS		TYP.	MAX.	UNIT
Static							
Drain-source breakdown voltage	V _{DS}	$V_{GS} = 0$, $I_D = 250 \mu A$		60	-	-	V
Gate-source threshold voltage	V _{GS(th)}	V _{DS} =	= V _{GS} , I _D = 250 μA	1.5	2.0	2.5	V
Gate-source leakage	I _{GSS}	V _{DS} =	0 V, V _{GS} = ± 20 V	-	-	± 100	nA
		V _{GS} = 0 V	V _{DS} = 60 V	-	-	1	
Zero gate voltage drain current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 60 V, T _J = 125 °C	-	-	50	μΑ
		V _{GS} = 0 V	V _{DS} = 60 V, T _J = 175 °C	-	-	150	
On-state drain current ^a	I _{D(on)}	V _{GS} = 10 V	V _{DS} ≥5 V	10	-	-	Α
		V _{GS} = 10 V	I _D = 2.3 A	-	0.125	0.150	
Daile and the said and a	В	V _{GS} = 10 V	I _D = 2.3 A, T _J = 125 °C	-	-	0.250	Ω
Drain-source on-state resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 2.3 A, T _J = 175 °C	-	-	0.325	
		V _{GS} = 4.5 V	I _D = 2.1 A	-	0.136	0.164	
Forward Transconductance b	9 _{fs}	V _{DS} :	V _{DS} = 15 V, I _D = 2.3 A		5.5	-	S
Dynamic ^b					•		
Input capacitance	C _{iss}			-	164	205	pF
Output capacitance	C _{oss}	V _{GS} = 0 V	V _{DS} = 30 V, f = 1 MHz	-	22	28	
Reverse transfer capacitance	C _{rss}			-	14	18	
Total gate charge c	Qg			-	3.5	5.3	
Gate-source charge c	Q _{gs}	V _{GS} = 10 V	$V_{DS} = 30 \text{ V}, I_{D} = 2 \text{ A}$	-	0.6	-	nC
Gate-drain charge ^c	Q _{gd}			-	0.7	-	1
Gate resistance	Rg		f = 1 MHz		5.84	9	Ω
Turn-on delay time c	t _{d(on)}			-	4	6	
Rise time ^c	t _r	$V_{DD} = 30 \text{ V}, \text{ R}_{L} = 15 \Omega$ $I_{D} \cong 2 \text{ A}, \text{ V}_{GEN} = 10 \text{ V}, \text{ R}_{g} = 1 \Omega$		-	9	13	1
Turn-off delay time ^c	t _{d(off)}			-	12	17	- ns
Fall time ^c	t _f			-	12	18	
Source-Drain Diode Ratings and Char	racteristics ^b	1			1		
Pulsed current ^a	I _{SM}			-	-	9	Α
Forward voltage	V _{SD}	I _F = 1.6 A, V _{GS} = 0		1	0.85	1.2	V

Notes

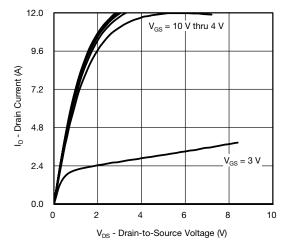
- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

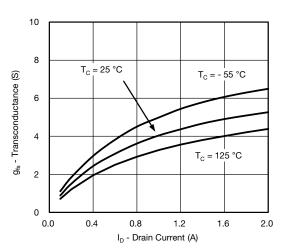


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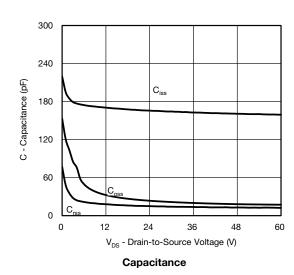
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

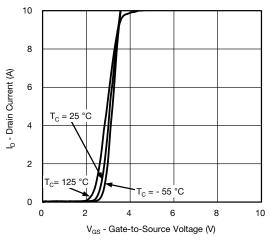


Output Characteristics

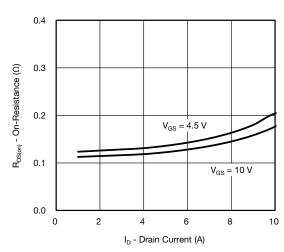


Transconductance

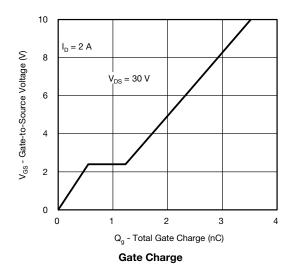




Transfer Characteristics



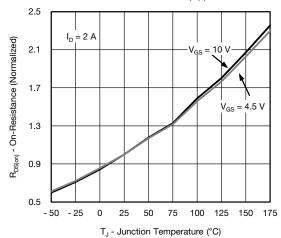
On-Resistance vs. Drain Current

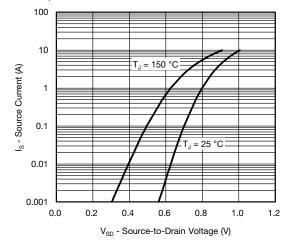




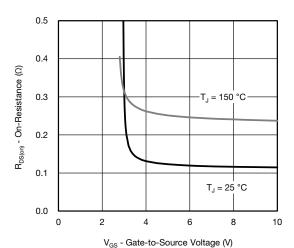
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TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

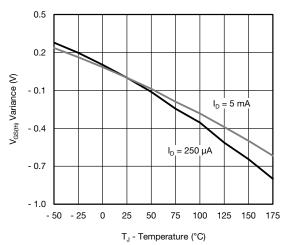




On-Resistance vs. Junction Temperature

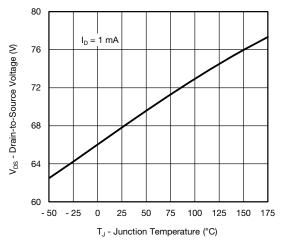


Source Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage

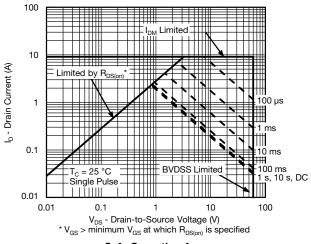




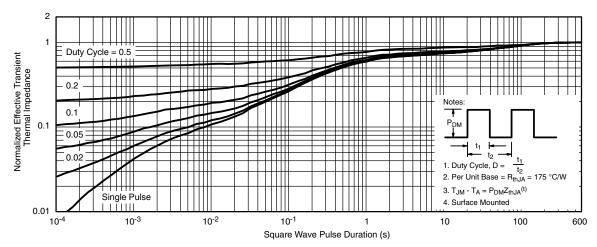
Drain Source Breakdown vs. Junction Temperature

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THERMAL RATINGS ($T_A = 25$ °C, unless otherwise noted)



Safe Operating Area

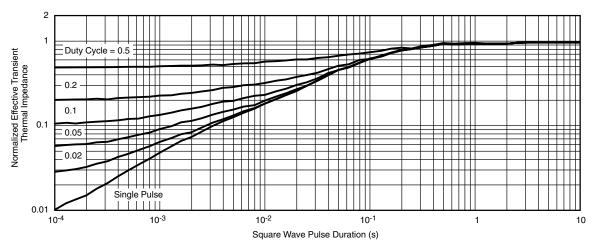


Normalized Thermal Transient Impedance, Junction-to-Ambient

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THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)

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Normalized Thermal Transient Impedance, Junction-to-Foot

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Foot (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

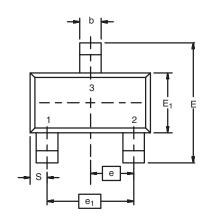
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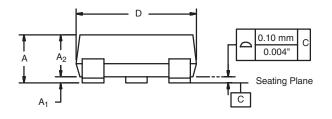


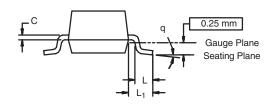
Package Information

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SOT-23 (TO-236): 3-LEAD







Dim	MILLIN	IETERS	INCHES			
	Min	Max	Min	Max		
Α	0.89	1.12	0.035	0.044		
A ₁	0.01	0.10	0.0004	0.004		
A ₂	0.88	1.02	0.0346	0.040		
b	0.35	0.50	0.014	0.020		
С	0.085	0.18	0.003	0.007		
D	2.80	3.04	0.110	0.120		
E	2.10	2.64	0.083	0.104		
E ₁	1.20	1.40	0.047	0.055		
е	0.95 BSC		0.0374 Ref			
e ₁	1.90	1.90 BSC		1.90 BSC 0.0748 Ref		8 Ref
L	0.40	0.60	0.016	0.024		
L ₁	0.64 Ref		0.025 Ref			
S	0.50 Ref		0.020 Ref			
q	3°	8°	3°	8°		
ECN: S-03946-Rev. K. 09-	Jul-01					

DWG: 5479

Document Number: 71196 09-Jul-01

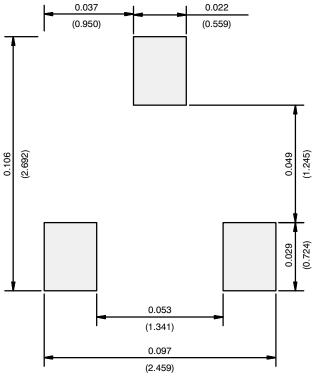
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Application Note 826

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RECOMMENDED MINIMUM PADS FOR SOT-23



Recommended Minimum Pads Dimensions in Inches/(mm)

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